

TOSHIBA Variable Capacitance Diode Silicon Epitaxial Planar Type

1SV287

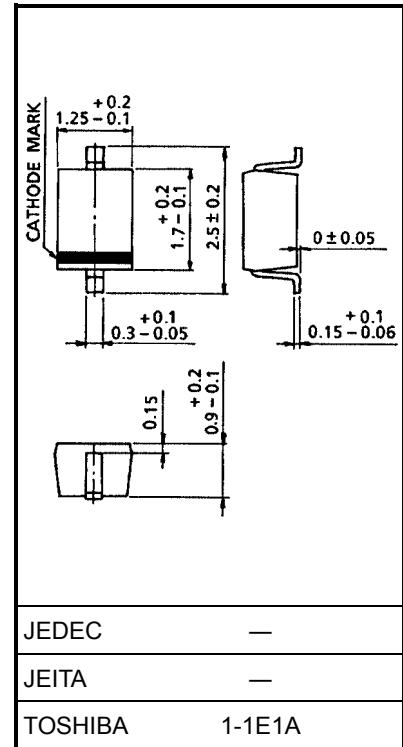
UHF SHF Tuning

- High capacitance ratio: $C_2 \text{ V}/C_{25} \text{ V} = 7.6$ (typ.)
- Low series resistance: $r_s = 1.9 \Omega$ (typ.)
- Excellent C-V characteristics, and small tracking error.
- Useful for small size tuner.

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	30	V
Peak reverse voltage	V_{RM}	35 ($R_L = 10 \text{ k}\Omega$)	V
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$

Unit: mm

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Weight: 0.004 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1 \mu\text{A}$	30	—	—	V
Reverse current	I_R	$V_R = 28 \text{ V}$	—	—	10	nA
Capacitance	$C_{2 \text{ V}}$	$V_R = 2 \text{ V}, f = 1 \text{ MHz}$	4.2	—	5.7	pF
Capacitance	$C_{25 \text{ V}}$	$V_R = 25 \text{ V}, f = 1 \text{ MHz}$	0.53	—	0.68	pF
Capacitance ratio	$C_{2 \text{ V}}/C_{25 \text{ V}}$	—	7.3	—	—	—
Series resistance	r_s	$V_R = 1 \text{ V}, f = 470 \text{ MHz}$	—	1.9	2.3	Ω

Note: Available in matched group for capacitance to 6%.

$$\frac{C(\text{max}) - C(\text{min})}{C(\text{min})} \leq 0.06$$

 $(V_R = 2 \sim 25 \text{ V})$

Marking

